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I. INTRODUCTION

 and conduction losses, the benefits of increased efficiency ى opp inverters requires increasing the switching frequency to min-ى imize the point of the point o ѓ of an LCL ye of a second ye a second ye of a second ye of a second ye of a second ye of a sec ى ated by the function of the fu the same inductance with fewer turns. The inverter side induc-ى tor, on the other ືing frequency of the second sec ቢ limits the weight/cost reduction [10], [11]. For example, a commercial high power SiC inverter is designed to switch only at 8 kHz [13]. In [14], the total filter size of a SiC inverter can be even larger than that of a Si-based counterpart. New design approaches are needed for inverters when SiC devices are adopted.

One approach for filter weight reduction is to increase the switching frequency to several hundreds of kHz so that highfrequency magnetic materials, however low-permeability, can be applied. In the medium to high power applications, hundreds of kHz switching frequency prefer soft switching technologies to further reduce switching loss [15]-[18]. For example, Z. Huang et al. designed a 25-kW SiC threephase inverter operated at critical conduction mode (CRM) to achieve zero-voltage-switching (ZVS) [15]. The switching frequency increased to above 300 kHz, and peak efficiency is close to 99%. The total LCL inductance is 10.3 μ H for each phase. A similar approach has also been discussed in [10] where Triangular Current Mode (TCM) is applied for a threephase inverter. CRM or TCM requires increasing the inverter side inductor current ripple to 100% to achieve zero-voltage turn-on, the cost is the increased turn-off loss and increased Root Mean Square (RMS) current flowing through switches, inverter side inductors, and output capacitors. Therefore this method is beneficial for medium to low power WBG converters as WBG devices usually have much smaller turn-off loss than turn-on loss. It has not been demonstrated for higher power applications that the reduced turn-on switching loss will still be beneficial with increased turn-off loss, conduction loss, and inductor loss caused by high current ripples. Another soft-switching method is to use an auxiliary switch assisted resonant circuit. N. He et al. presented a 20-kW ZVS SiC inverter with 98.74% peak efficiency in [18] where the ac side inductance is 33 μ H, and auxiliary inductance is 2 μ H when switched at 300 kHz. Compared with a hard-switched inverter at 100 kHz switching frequency, the total inductor volume of this ZVS inverter has been reduced from 1.14 liters to about 0.5 liters. Although these high switching frequency based designs have shown effective inductor size reduction, it will lead to a new design issue because the switching frequency will fall into the EMI frequency range (150 kHz to 30 MHz). As EMI standards usually have much higher harmonic suppression requirements than utility code [19], switching faster than 150 kHz will bring more challenges to EMI noise suppression and/or CM chock design [20].

In the authors' previous work [25], a filter-less five-level (5L) SiC inverter was proposed to reduce the weight for a 60-kW three-phase PV string inverter. The basic topology is a three-level T-type $(3LT^2)$ circuit, which is well adapted in the PV industry [21]-[24]. Two 3LT² circuits were interleaved with an intercell transformer (ICT) to form a 5L output 99.2% has been achieved for this 60-kW PV string inverter. This paper aims to increase the power rating of the proposed PV inverter to 100-kW without increasing the weight. To further improve the efficiency and specific power, the passive components need to be optimized. Also, the SiC MOSFETs need to be switched faster without false triggering. The paper focuses on solving the above-mentioned design challenges. Section II presents the closed-form equations of highfrequency DM voltage, CM voltage, and dc side current harmonics of proposed 100-kW PV string inverter. These equations are used at the early design stage to prevent the overdesign of passive components. In Section III, the optimization procedure of ICTs is provided with a design case and closedform equations. The analysis in Section III also presents a new aspect of ICT design: the weight of an ICT is directly related to the accuracy of circulating current control. The analysis ేshows the function of the fun switching frequency increases. This feature makes the ICT more preferable for high switching frequency applications over conventional LCL inductors, in which the specific core loss will increase with switching frequency. Section IV focus ేon how to prevent the prevent to p conventional false triggering issue can be identified at the double pulse testing stage and can be prevented with proper gate driver isolations. However, a different phenomenon has been identified in this paper, which can also lead to false triggering. This phenomenon, named as the inter-phase crosstalk issue, will only happen when there are multiple phase legs switching ॅ, togge analysis (FEA) based circuit parasitic extraction and compared with vector network analyzer (VNA) measurements. An improved PCB design is then proposed to solve the new discovered inter-phase crosstalk issue. A 100-kW PV string inverter has been built in the laboratory. The total weight of the 100-kW dc/dc and dc/ac two-stage prototype is less than 20 kg where the total weight of ICTs is less than 2.5 kg. The measured CEC weighted efficiency is 99.2% with a peak efficiency of 99.5% at 720 V input.

II. AN ANALYTICAL BASED PASSIVE COMPONENTS SELECTION METHOD



FIGURE 1. The 100-kW two-stage SiC 5LT² filter-less PV string inverter.



FIGURE 2. One phase schematic of $5LT^2$ inverter where s_{x1} , s_{x2} , s_{x3} , s_{x4} are switching functions and $x \in \{a, b, c\}$.

components is usually an iterative task that needs multiple inputs including environmental conditions, operation profile, lifetime requirement, and cost constraint. These inputs vary from design to design. But the common factors for passive components design are the current stress and voltage stress. As the parasitics, power loss, and lifetime of passive components are all frequency-dependent, it is desirable to derive current and voltage stress in the frequency domain. In this section, the spectrums of dc link current and ac side voltage for this three-phase 5LT² inverter are derived analytically. As the equations are in closed-form, they can apply to 5LT² inverters at any desired operating conditions. The analysis in this section also quantifies the significant reduction of harmonics compare to those of three-level inverters.

A commercial PV string inverter usually includes dc/dc stage and dc/ac stage. The topology of the proposed SiC 100-kW PV string inverter is shown in Fig. 1. The dc/dc stage consists of four SiC interleaved boost circuits. The dc/ac stage is a three-phase 5LT² inverter with six 1200 V SiC T-type modules provided by Wolfspeed. Every two modules are parallel-coupled through an ICT to form one phase that has five-level line-to-neutral output voltage [25], [26].

The four switching functions of one phase $5LT^2$ inverter are defined as s_{x1} , s_{x2} , s_{x3} , s_{x4} , which are shown in Fig. 2. Switching states corresponding to different voltage levels are listed in Table 1. The redundant switching states in Lv1, Lv2, and Lv3 are used for ICT circulating current control. One way to generate the switching signals for the $5LT^2$ inverter is to interleave the carriers of two $3LT^2$ inverters. The upper and lower carriers of a 3L carrier-based modulation can be placed in the same direction or in the opposite direction, which are named phase disposition (PD) modulation and phase opposition disposition (POD) modulation, respectively. The key waveforms of the $5LT^2$ inverter are presented in Fig. 3.



TABLE 1. Switching States of One Phase of the 5LT² Inverter

FIGURE 3. Waveforms of v_{DM} , v_{CM} , v_{ICT} , i_{cap} (carrier ratio reduced 10 times for easy observation).

The carrier ratio is reduced by 10 times for easy observation. v_{DM} , v_{CM} , v_{ICT} , i_{cap} are DM voltage, CM voltage, ICT winding voltage, and dc neutral point current, respectively.

Although 3L PD and POD modulation generate different voltage spectrums, with the method from [25], it can be proved that both modulations will generate a voltage spectrum that is the same as 5L alternative phase opposition disposition (APOD). The line-to-neutral voltage spectrum of interleaved modulation is defined as v_x , $x \in \{a, b, c\}$, which can be derived as:

$$v_x(t) = V_{dc}M\cos\omega_o t$$

+ $\frac{V_{dc}}{\pi}\sum_{m=1}^{\infty}\frac{1}{m}\sum_{n=-\infty}^{\infty}J_{2n+1}\left(2m\pi M\right)\cos\left(n\pi\right)$
× $\cos\left(2m\omega_c t + [2n+1]\cdot[\omega_o t + \theta_x]\right)$ (1)

where V_{dc} is the half dc-link voltage, M is the modulation index, ω_o and ω_c are the fundamental and carrier angular frequency, respectively, with m, n being the harmonic order for carrier frequency and fundamental frequency. $J_n()$ is the n-th order Bessel function of the first kind where $x \in$ $\{a, b, c\}, \theta_a = 0, \theta_b = -2\pi/3, \theta_c = +2\pi/3$. The harmonics are always odd sidebands around the even carrier multiples, therefore the equivalent switching frequency is twice the actual switching frequency. In (1) and the following equations in this paper, the reference zero potential point for circuit analysis is chosen as the dc capacitor neural, which is the point 0 in Fig. 2.

Derived from (1), the line-to-line voltage spectrum is shown in (2) shown at the bottom of the next page, where The voltage spectrum of ICT is derived as:

$$v_{ICT}(t) = \frac{4V_{dc}}{\pi} \sum_{m=0}^{\infty} \frac{1}{2m+1} \sum_{n=-\infty}^{\infty} J_{2n+1} \left[(2m+1)\pi M \right]$$
$$\cdot \cos(n\pi) \cos([2m+1]\omega_c t + [2n+1]\omega_o t) \quad (3)$$

From (3) it can be observed that there is no low-frequency harmonics applied on ICT, v_{ICT} only contains odd sidebands around the odd carrier multiples.

The high-frequency CM voltage needs to be derived for ground leakage current suppression or CM voltage reduction purpose, which is shown below:

$$v_{CM_HF}(t) = \frac{V_{dc}}{3} [s_a(t) + s_b(t) + s_c(t)]$$

= $\frac{V_{dc}}{\pi} \sum_{m=1}^{\infty} \frac{1}{m} \sum_{n=-\infty}^{\infty} J_{3\cdot(2n+1)}(2m\pi M) \cos(3n+1)$
 $\times \pi \sin[2m\omega_c t + 3(2n+1)\omega_0 t]$ (4)

$$I_{DC}(\omega) = \frac{I_o}{2} \left[e^{j\emptyset} S_1(\omega - \omega_o) + e^{-j\emptyset} S_1(\omega + \omega_o) \right]$$
(5)

$$i_{cap}(t) = i_{an}(t) + i_{bN}(t) + i_{c_N}(t)$$

=
$$\sum_{x \in a, b, c} [s_{x1}(t) - s_{x2}(t) + s_{x3}(t) - s_{x4}(t)] \cdot i_x(t)$$

(6)

In the frequency domain, (6) is transferred into convolution shown in (7):

$$I_{cap}(\omega) = \sum_{x \in a, b, c} [S_{x1}(\omega) - S_{x2}(\omega) + S_{x3}(\omega) - S_{x4}(\omega)] \otimes I_x(\omega)$$
(7)

Equation (8) can then be derived from (5) and (7):

$$I_{cap}(\omega) = \frac{I_o}{2} \sum_{x \in a,b,c} \left[e^{j\emptyset} S_{x1}(\omega - \omega_o) + e^{-j\emptyset} S_{x1}(\omega + \omega_o) - e^{j\emptyset} S_{x2}(\omega - \omega_o) - e^{-j\emptyset} S_{x2}(\omega + \omega_o) + e^{j\emptyset} S_{x3}(\omega - \omega_o) + e^{-j\emptyset} S_{x3}(\omega + \omega_o) - e^{j\emptyset} S_{x4}(\omega - \omega_o) - e^{-j\emptyset} S_{x4}(\omega + \omega_o) \right]$$

$$(8)$$

Therefore, the dc neutral point current spectrum of one phase leg can be calculated as:

$$i_{xN}(t) = \frac{I_o}{4} \left\{ \left(\frac{10M}{3\pi} - 1 \right) \cos \left(\omega_o t + \theta_x \right) - \frac{8M}{\pi} \sum_{n=3}^{\infty} \frac{(1 - \cos (n\pi)) \sin \left(\frac{n\pi}{2} \right)}{n \left(n^2 - 4 \right)} \cos \left(n \omega_o t + n \theta_x \right) + \sum_{m=1}^{\infty} \sum_{n=-\infty}^{\infty} C_{2m-1, \ 2n} \cos \left([2m-1] \left[\omega_c t + \theta_c \right] + 2n \left[\omega_o t + \theta_x \right] \right) + \sum_{m=1}^{\infty} \sum_{n=-\infty}^{\infty} C_{2m,2n+1} \times \cos(2m \left[\omega_c t + \theta_c \right] + [2n+1] \left[\omega_o t + \theta_x \right]) \right\}$$
(9)

$$C_{2m-1,2n} = \frac{2\cos(n\pi)}{(2m-1)\pi} \times \{J_{2n+1}\left([2m-1]\pi M\right) - J_{2n-1}\left([2m-1]\pi M\right)\}$$
(10)

$$v_{ab}(t) = v_a(t) - v_b(t) = \sqrt{3}V_{dc}M\cos\left(\omega_o t + \frac{\pi}{6}\right) + \frac{\sqrt{3}V_{dc}}{\pi}\sum_{m=1}^{\infty}\frac{1}{m}\sum_{n=-\infty,2n+1\neq 3k,\ k\ integer}^{\infty}J_{2n+1}(2m\pi M)\cos(n\pi) \\ \times \cos\left(2m\omega_c t + [2n+1]\cdot\left[\omega_o t + \theta_x + \frac{\pi}{6}\right]\right) = \sqrt{3}v_{DM}(t)$$
(2)

$$C_{2m,2n+1} = \frac{4\cos(n\pi)}{m\pi^2} \left\{ \sum_{k=1}^{\infty} (2k-1) \cdot J_{2k-1}(2m\pi M) \\ \cdot \left[\frac{1}{(2k+2n-1)(2k-2n-1)} \\ - \frac{1}{(2k+2n+1)(2k-2n-3)} \right] \right\}$$
(11)

)

Equation (9) contains odd-order fundamental harmonics, even- and odd-order switching harmonics and their sidebands. With the interleaved phase legs, the combined dc current harmonics of one phase leg contains odd-order fundamental harmonics, even-order switching harmonics sidebands. With all six phase legs from three phases, the dc current spectrum only contains $3n\omega_o$ and $2m\omega_c \pm 3k\omega_o$ harmonic components, which is derived as:

$$i_{cap}(t) = \frac{3I_o}{2} \left[\frac{16M}{\pi} \sum_{\substack{n=1, \\ n \text{ is odd}}}^{\infty} \frac{1}{3n(9n^2 - 4)} \cos(3n\omega_o t) + \sum_{m=1}^{\infty} \sum_{\substack{n=-\infty}}^{\infty} C_{2m,3(2n+1)} \cdot \cos(2m\omega_c t) + 3[2n+1]\omega_o t) \right]$$
(12)

$$C_{2m,3(2n+1)} = \frac{4\cos(3n\pi)}{m\pi^2} \left\{ \sum_{k=1}^{\infty} (2k-1) J_{2k-1} (2m\pi M) \\ \cdot \left[\frac{1}{(2k+6n+1)(2k-6n-3)} - \frac{1}{(2k+6n+3)(2k-6n-5)} \right] \right\}$$
(13)

Equation (12) covers both low frequency and high frequency. It can be used for sizing electrolytic and film capacitors. (12) shows the switching frequency components disappeared, and only part of the sidebands remain at $2\omega_c$.

The above analysis is based on interleaved modulation. The spectrum of interleaved modulation is equivalent to 5L alternative phase opposition disposition (APOD). In some cases, 5L PD modulation is preferred for smaller line-to-line voltage harmonics. To achieve 5L PD or POD, a state-machine based modulation method and its analysis can be found in [30] and [31]. The dc-link current spectrum of 5L PD and POD can be derived following the same procedure from (6) to (12).

The above equations are utilized to find the closed-form spectrum expressions of key circuit waveforms, as they are not currently available from literature for this $5LT^2$ topology and were not derived in the authors' previous work [25], [28]. Equation (1)–(4) and (12) saved the time-consuming task of

finding the spectrum of v_{DM} , v_{CM} , v_{ICT} , i_{cap} under different operation conditions through iterations of simulations. Instead, these viable can be quickly calculated via Matlab or python script so that a software design tool can be developed to automatically select the passive components.

Compared with 2L or 3L inverters, $5LT^2$ inverters have smaller voltage harmonics at ac side and smaller current harmonics at dc side. A frequency-weighted RMS value of v_{DM} , v_{CM} , i_{cap} are defined in (14)–(16) to further simplify the design process. This frequency-weighted RMS definition specifies the high order switching harmonics referring to the switching frequency, so it reflects the impedance needed to suppress the RMS value exactly to a required design target. As a result, the passive component is proportional to its frequency-weighted RMS (WRMS) value and will not be overdesigned.

$$V_{DM,WRMS} = \frac{1}{\sqrt{2}} \cdot \sqrt{\sum_{m=1}^{\infty} \sum_{n=-\infty}^{\infty} \left(\frac{V_{DM,mn}}{m}\right)^2} \quad (14)$$

$$V_{CM,WRMS} = \frac{1}{\sqrt{2}} \cdot \sqrt{\sum_{m=1}^{\infty} \sum_{n=-\infty}^{\infty} \left(\frac{V_{CM,mn}}{m}\right)^2} \quad (15)$$

$$I_{cap,WRMS} = \frac{1}{\sqrt{2}} \cdot \sqrt{\sum_{m=1}^{\infty} \sum_{n=-\infty}^{\infty} \left(\frac{I_{cap,mn}}{m}\right)^2} \quad (16)$$

As an example, the required CM inductance to suppress the ground leakage current, defined as $(i_a + i_b + i_c)/3$, can be calculated using the following steps:

- Obtain CM RMS current limitation *I_{CM,RMS}* from utility code or application requirements.
- 2) Derive the low frequency component of ground leakage current $I_{CM,RMS,LF}$ [28] and calculate the high frequency limitation by $I_{CM,RMS,HF} = \sqrt{I_{CM,RMS}^2 I_{CM,RMS,LF}^2}$.
- 3) Calculate the CM inductance using $L_{CM} = \frac{V_{CM,WRMS}}{I_{CM,RMS,HF} \cdot \omega_C}$.

It should be noted that WRMS only contain high frequency components. The low frequency ground leakage current is suppressed through control [28]. In (14)-(16), each of the terms will decrease fast as m and n increases. Therefore only a limited number of m and n need to be calculated. With equation (1)–(4), (12), and (14)–(16), the weighted RMS value can be calculated for DM voltage, CM voltage, and dc-link capacitor current, as shown in Fig. 4. Compared with $3LT^2$ inverters, the frequency-weighted DM voltage switching harmonics of the 5LT² inverter, at 800 V, is reduced to 26.1%, the frequency-weighted CM voltage switching harmonics is reduced to 7.9%, and the frequency-weighted dc-link capacitor current switching harmonics is reduced to 5.6%. Fig. 4 leads to a lightweight design that no DM power filter is needed, CM choke can be designed with a small size and the number of metal film capacitors can be reduced. Therefore, the specific power of 10 kW/kg is achieved for inverter stage only and 5 kW/kg achieved for a 100-kW 2-stage PV string inverter.



FIGURE 4. Comparison of switching harmonics between $3LT^2$ and $5LT^2$ inverter. (a) $V_{DM,WRMS}$, (b) $V_{CM,WRMS}$, and (c) $I_{cap,WRMS}$ (condition: 480 Vac 100 kW output, switching frequency 50 kHz).

III. ICT DESIGN OPTIMIZATION

A. DERIVING THE MINIMUM MASS OF THE MAGNETIC CORE

To prevent ICT from saturation, (17) must be met.

$$\Delta B (\max) + B_{bias} < B_{sat}$$

where $\Delta B (\max) = \frac{V_{dc}T_s}{4NA_e}, B_{bias} = \frac{N}{A_eR_m} \cdot I_{bias}$ (17)



FIGURE 5. ICT turns number range vs. switching frequency. (a) at different dc-link voltage, and (b) at different circulating current.

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$$N \in \left[\frac{B_{sat}A_eR_m - \sqrt{B_{sat}^2A_e^2R_m^2 - V_{dc}I_{bias}T_sR_m}}{2I}, \\ \times \frac{B_{sat}A_eR_m + \sqrt{B_{sat}^2A_e^2R_m^2 - V_{dc}I_{bias}T_sR_m}}{2I}\right]$$
(18)





FIGURE 6. The waveforms of magnetic flux density and voltage applied to the ICT in a quarter line cycle, with the carrier ratio reduced for easy observation.

Based on this principle, the minimum mass of ICT can be derived accordingly.

To make sure there is a positive real number N, the condition $B_{sat}^2 A_e^2 R_m \ge V_{dc} I_{bias} T_s$ must be met, which results in (19).

$$I_{bias} \le \frac{B_{sat}^2 A_e^2 R_m f_s}{V_{dc}} \tag{19}$$

In this research, I_{bias} of each ICT are sensed by differential current sensors, and controlled by a closed-loop controller in parallel with the output current controller [25]. Therefore, the mass of the ICT core is a function of power rating, switching frequency, core material and the error of I_{bias} control shown in (20).

$$mass \ge e\% \cdot \frac{\mu_{avg}\rho_V}{k_v B_{sat}^2} \cdot \frac{P_o}{3Mf_s}$$
(20)

Equation (20) is derived from (19), where $k_v = (A_e \cdot MPL)/Volume$ is the volume correction coefficient. e% is the percentage of circulating current referred to fundamental current. *M* is the modulation index. *MPL* is the magnetic pass length. ρ_V is the volumetric mass density. μ_{avg} is the averaged permeability, it can be replaced with the permeability of the core when the air gap is small enough.

Equation (20) is the scale-law for ICT, it can be used to choose a baseline core size as the starting point of loss optimization. Since (20) is derived from (18), the selected baseline core will meet the non-saturation range defined in Fig. 5. (20) also shows that, increasing switching frequency can directly reduce the mass of ICT. It is equally important to increase the accuracy of circulating current control, as the amount of circulating current is in a linear relationship with the mass of ICT.

B. ICT POWER LOSS OPTIMIZATION

The magnetic flux density waveform of ICT is shown in Fig. 6. It has two unique features: Firstly, unlike inductors in grid-connected voltage source converters (VSC), there is no fundamental frequency flux density in ICT cores. Therefore the trajectory in the BH plane can be treated as a group of closed curves; no minor loop separation is needed [34]. The



FIGURE 7. ICT Performance under different sample points in each switching cycle. (a) Magnetic flux design plots. (b) Calculation time and error (CPU: i7-4770 RAM: 8 GB).

core loss characteristics of ICT is simpler than that of an ac inductor in VSC. Second, compared with a high-frequency transformer, the ICT is also excited with rectangular voltage, but the duty ratio is different in each switching cycle.

The core loss of ICT can be calculated using iGSE method [34] by (21).

$$\overline{P_{core}} = \frac{1}{T} \int_{0}^{T} k_i \left| \frac{dB}{dt} \right|^{\alpha} (\Delta B)^{\beta - \alpha} dt$$
$$k_i = \frac{k}{(2\pi)^{\alpha - 1} \int_{0}^{2\pi} |\cos\theta|^{\alpha} 2^{\beta - \alpha} d\theta}$$
(21)

The iGSE method can provide enough accuracy under nonsine excitation, and only Steinmetz parameters (k, α, β) are needed. In this application, as the duty ratio of ICT voltage is constantly changing, numerical calculations are required [35]. To achieve enough accuracy, hundreds of data points in each switching cycle is necessary, as shown in Fig. 6. Therefore, the calculation time for high switching frequency application can reach to several hours for one design, which limits its application in ICT design optimization for the proposed 100-kW SiC PV inverter.

Since the converter is controlled in such way that the voltseconds applied on ICT always returns to zero within one switching cycle, then equation (21) can be further simplified based on the fact of dB/dt being constant. In addition, only a quarter of the line cycle needs to be calculated since the ICT voltage is symmetrical across [0, pi/4, pi/2, 3pi/4] of each line cycle. Thereby a simplified core-loss calculation method is derived as (22):

$$\overline{P_{core}} = 4k_i f_o \left(\frac{V_{dc}}{NA_e}\right)^{\beta} \sum_{n=1}^{\frac{f_s}{2f_o}} \Delta T_{on}(n)^{\beta-\alpha+1}$$
$$= 4k_i f_o f_s^{\alpha-\beta-1} \left(\frac{V_{dc}}{NA_e}\right)^{\beta} \sum_{n=1}^{\frac{f_s}{2f_o}} d_{ICT}(n)^{\beta-\alpha+1}$$
(22)

where $\overline{P_{core}}$ is the averaged specific core loss. $\Delta T_{on}(n) = T_{inv1}(n) - T_{inv2}(n)$ is the time duration when the voltage applied on ICTs at the *n*-th switching cycle, which is the difference of on-times of the two interleaved inverter legs. $d_{ICT} = \Delta T_{on}/T_s$, is the duty ratio of ICT voltage waveform. Sum of



FIGURE 8. ICT power loss calculation with different turns at multiple switching frequencies.



FIGURE 9. ICT power loss vs. turns at different core size.



FIGURE 10. The photo of an ICT hardware for the 100-kW PV inverter application.



FIGURE 11. Gate driver power and signal path structure.

The current flowing through ICT windings is dominated by fundamental frequency current. Thereby the winding loss can be calculated by (23).

$$P_{wire} = 0.25I_{RMS}^2 R_{wire}$$

= $0.25I_{RMS}^2 \cdot \rho N \frac{MLT}{CopperHeight \times CopperWidth}$
(23)

With (22) and (23), the core loss and winding loss can be calculated. By sweeping the switching frequency and number of turns within the allowable filling factor, the minimal ICT loss can be found, as shown in Fig. 8. Fig. 8 shows the ICT power loss will decrease when switching frequency increases. Fig. 9 presents the power loss of ICT designed with different core sizes. It should be noted that: increasing the size of core doesn't always result in reducing power loss. For example,

when increasing core mass from 567 g to 680 g, the total power loss nearly unchanged.

IV. INTER-PHASE CROSSTALK MITIGATION

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FIGURE 12. The inter-phase crosstalk phenomenon. (a) Experimental waveforms with original PCB design. Failed at 150V input. (b) Schematic. (c) The circuit schematic of two phase legs with parasitic parameters. (d) Equivalent circuit model.

Fig. 12(a) is the experiment waveform demonstrating this inter-phase crosstalk issue. When the dc-link voltage increased to 150 Vdc, this crosstalk issue caused shoot-through of a phase leg, and de-sat protection was triggered. In Fig. 12(a), CH1 and CH2 are output voltage waveforms of the two interleaved phase legs from phase A, namely v_{A1} and v_{A2} , respectively. CH3 and CH4 are the phase B voltage waveforms v_{B1} and v_{B2} . CH5 is the 5L voltage of the combined phase C1 and C2 legs (after ICT). CH6 is the current of T4 switch in phase C1. Fig. 12(a) shows that the overcurrent event of phase C1 happened when phase A legs were switching but phase C legs were not switching. Thereby the shoot-through in phase C had time correlation with the switching event from phase A. To rule out other propagation paths, the gate drivers' power supplies of different phase legs were changed to individual batteries that were isolated from each other. In addition, the gating signals were optical isolated. Therefore, the remaining propagation path was through the main power circuit. By cutting the PCB traces to isolate different propagation paths one by one, the signal propagation path was found to be through the ac terminal parasitic capacitance. Fig. 12(b) is the circuit schematic of two phase legs with parasitic parameters showing the propagation path.

To analyze this interphase crosstalk phenomenon, the parasitic parameters of the original PCB board is extracted and an LTspice model is built accordingly. The impedance of the PCB circuit model is simulated and compared with the vector network analyzer (VNA) measurement results to verify the accuracy of extraction. This modeling procedure is shown in Fig. 13. The top three pictures in Fig. 13 show the modeling



FIGURE 13. Method to extract and verify the PCB parasitic.



FIGURE 14. Rearrange PCB layout to solve inter-phase crosstalk issue.

procedure. The PCB busbar is modeled as a multi-port passive circuit. The impedances of the ports are simulated and then compared with impedance measured by VNA. It can be found from the PCB model that to reduce this interphase crosstalk requires to suppress the transfer gain from one phase leg to another. Although there are multiple solutions to achieve this goal, we choose to re-arrange the PCB layers. In this way, the dimension of PCB will not change, and the locations of the main power components will not change. Fig. 14 shows the improved PCB layout to increase the parasitic capacitance on T4, in turn to reduce the transfer gain from another phase leg. The improved PCB design is shown in Fig. 15. Fig. 15(a) is the simulated gate voltage waveforms using the LTspice model of original PCB and improved PCB. Fig. 15(b) is the experiment waveforms showing the inverter can operate at 830 V dc-link continuously with improved PCB design.

V. PROTOTYPE AND EXPERIMENT RESULTS



FIGURE 15. Results of improved PCB design. (a) Spice model simulation of gate voltage using extracted PCB parameters. (b) Experimental waveforms of the inverter output voltage at 830 V dc-link voltage.



FIGURE 16. The 100-kW 2-stage SiC filter-less PV string inverter prototype.

TABLE 2. 100-kW SiC PV Inverter Specifications

Parameters	Values
Nominal output power	$P_o = 100 \text{ kW}$
DC-link voltage	$2V_{dc} = 720 \text{ V} \sim 850 \text{ V}$
Output voltage (line-to-line)	$v_g = 480 \text{ V rms}$
Output frequency	$f_o = 60 \text{ Hz}$
Boost switching frequency	$f_{Boost} = 75 \text{ kHz}$
Inverter switching frequency	$f_{Inv} = 50 \text{ kHz}$
Boost inductance	$L_{Boost} = 400 \ \mu H$
ICT magnetizing inductance	$L_{ICT} = 9 \text{ mH}$
ICT leakage inductance	$L_{DM} = 10 \ \mu \text{H}$
CM inductance	$L_{CM} = 240 \ \mu \text{H}$
DC-link capacitance	$C_{dc} = 2.1 \text{ mF}$
Cooling	forced air cool
Dimension	18.5" x 17" x 7"
Weight	19.7 kg
Specific power (two-stage)	5.07 kW/kg, 2.3 kW/lb
Power density (two-stage)	2.8 kW/L, 45.4 W/in ³
Boost inductor weight	815g x 4
ICT weight	822g x 3
CM chock weight	229g

about 35 meters of AWG 0 cable. The measured total inductance, including the transformer leakage inductance and the cable inductance, is 120 μ H in each phase. The key wave-includes the half dc-link voltage, output line-to-line voltage, output line to neutral voltage, and output current. The stand-ॅ of of oth bank directly connected to the three-phase output of the inverter, without any filter in between. The measured dc-link voltage ripple is 53.5 V. It should be noted that the line-to-line voltage is also used in the grid-tied control for grid synchro-amount of carrier frequency harmonics, a second-order analog filter is used in the signal conditioning circuit. It can and connection cable. In the grid-connected mode, the measured current THD is 2.41% at 85% load ratio, with the grid voltage THD being 3.53%.





FIGURE 17. Stand-alone experimental waveforms. (a) Half dc-link voltage, output line-to-line voltage, output line-to-neutral voltage, and output current. (b) Three-phase line-to-neutral voltage and output current ripple.



FIGURE 18. Grid-connected experimental waveforms.

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FIGURE 19. CM choke for ground leakage current suppression. 240 μH @100 kHz, 229 g.



FIGURE 20. Ground leakage current experimental results. PV panel ground capacitance: 12 μ F each; CM choke: 240 μ H; Ground leakage current: 205 mA.



FIGURE 21. Measured efficiency of the 100-kW 5LT² inverter.

at 1 kHz. A thermal image of the converter running at full load is presented in Fig. 22. The hottest area is where the power module attached to the heatsink, with a temperature reading of 62 degrees Celsius. The weight breakdown and power loss breakdown is illustrated in Fig. 23.



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FIGURE 23. Loss breakdown and weight breakdown.

VI. CONCLUSION

for a three-phase high power string PV inverter adopting SiC MOSFETs. This design is free of the conventional LCL-type power filter. This design is suitable for high power highfrequency inverter applications as the size of passive components will be much smaller than the conventional design. The experimental verifications have been demonstrated on a 100kW filter-less PV inverter prototype. This 2-stage prototype is speed. The measured weight of this two-stage prototype is less than 20 kg, which includes the weight of the power circuit, cooling system, wireless communication, and auxiliary power supply. Therefore the specific power of 10 kW/kg is achieved for inverter stage only and 5 kW/kg achieved for a 100-kW 2-stage PV string inverter. Experimental results have shown a 2.41% current THD measured in a grid with 3.53% voltage CEC efficiency under 720 V input voltage is 99.2%, and the peak efficiency is 99.5%.

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